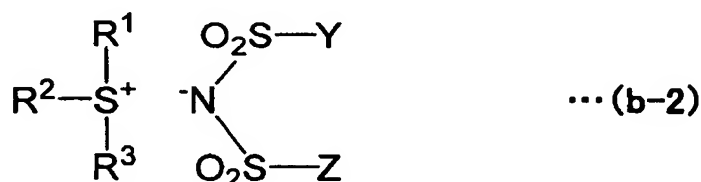
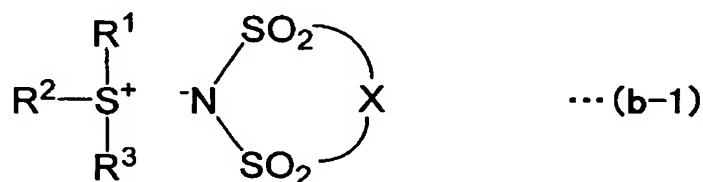


## CLAIMS

1. A resist composition, comprising a resin component (A) that undergoes a change in alkali solubility under action of acid, and an acid generator component (B) that  
 5 generates acid on exposure, wherein

said component (A) is a resin with a weight average molecular weight of no more than 8,000 which comprises structural units (a) derived from a (meth)acrylate ester, and  
 said component (B) comprises at least one sulfonium compound represented by a general formula (b-1) or a general formula (b-2) shown below:

10 [Formula 1]



[wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represent, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen

15 atom has been substituted with a fluorine atom;  $\text{R}^1$  to  $\text{R}^3$  each represent, independently, an aryl group or an alkyl group, and at least one of  $\text{R}^1$  to  $\text{R}^3$  represents an aryl group].

2. A resist composition according to claim 1, wherein said component (B) also comprises an onium salt-based acid generator containing a straight-chain fluorinated alkylsulfonate ion of 1 to 7 carbon atoms as an anion.
- 5 3. A resist composition according to claim 1, wherein said structural units (a) have structural units (a1) derived from a (meth)acrylate ester containing an acid dissociable, dissolution inhibiting group.
4. A resist composition according to claim 3, wherein said structural units (a) also  
10 have structural units (a2) derived from a (meth)acrylate ester containing a lactone-containing monocyclic or polycyclic group.
5. A resist composition according to claim 3, wherein said structural units (a) also have structural units (a3) derived from a (meth)acrylate ester containing a polar group-  
15 containing aliphatic hydrocarbon group.
6. A resist composition according to claim 1, further comprising a nitrogen-containing organic compound.
- 20 7. A method for forming a resist pattern, comprising the steps of forming a resist film on a substrate using a resist composition according to claim 1, conducting selective exposure treatment of said resist film, and then conducting alkali developing to form said resist pattern.
- 25 8. A resist pattern formed using a method according to claim 7.